Mark Hopkinson

List of Publications by Year
in descending order

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622 papers	11,456 citations	29994 54 h-index	53109 85 g-index
623 all docs	623 docs citations	623 times ranked	5400 citing authors

#	Article	IF	Citations
1	Inverted Electron-Hole Alignment in InAs-GaAs Self-Assembled Quantum Dots. Physical Review Letters, 2000, 84, 733-736.	2.9	467
2	Improved performance of 1.3Î¼m multilayer InAs quantum-dot lasers using a high-growth-temperature GaAs spacer layer. Applied Physics Letters, 2004, 85, 704-706.	1.5	267
3	Nature of the Stranski-Krastanow Transition during Epitaxy of InGaAs on GaAs. Physical Review Letters, 2001, 86, 2381-2384.	2.9	241
4	Experimental investigation of the effect of wetting-layer states on the gainâ€“current characteristic of quantum-dot lasers. Applied Physics Letters, 2002, 81, 4904-4906.	1.5	205
5	Determination of the shape and indium distribution of low-growth-rate InAs quantum dots by cross-sectional scanning tunneling microscopy. Applied Physics Letters, 2002, 81, 1708-1710.	1.5	200
6	Optimizing the growth of 1.3 Î¼m InAs/InGaAs dots-in-a-well structure. Journal of Applied Physics, 2003, 93, 2931-2936.	1.1	180
7	Electronic energy levels and energy relaxation mechanisms in self-organized InAs/GaAs quantum dots. Physical Review B, 1996, 54, 17738-17744.	1.1	165
8	Charged and neutral exciton complexes in individual self-assembledIn(Ga)Asquantum dots. Physical Review B, 2001, 63, .	1.1	164
9	Emission spectra and mode structure of InAs/GaAs self-organized quantum dot lasers. Applied Physics Letters, 1998, 73, 969-971.	1.5	152
10	Observation of multicharged excitons and biexcitons in a single InGaAs quantum dot. Physical Review B, 2001, 63, .	1.1	142
11	High-performance three-layer 1.3-/spl mu/m InAs-GaAs quantum-dot lasers with very low continuous-wave room-temperature threshold currents. IEEE Photonics Technology Letters, 2005, 17, 1139-1141.	1.3	136
12	Fast Optical Preparation, Control, and Readout of a Single Quantum Dot Spin. Physical Review Letters, 2008, 100, 197401.	2.9	133
13	Nuclear Spin Switch in Semiconductor Quantum Dots. Physical Review Letters, 2007, 98, 026806.	2.9	122
14	1.3â€…[micro sign]m InAsâˆ•GaAs multilayer quantum-dot laser with extremely low room-temperature threshold current density. Electronics Letters, 2004, 40, 1412.	0.5	120
15	Long-wavelength light emission and lasing from InAsâˆ•GaAs quantum dots covered by a GaAsSb strain-reducing layer. Applied Physics Letters, 2005, 86, 143108.	1.5	120
16	Stranski-Krastanow transition and epitaxial island growth. Physical Review B, 2002, 66, .	1.1	117
17	Fine structure of charged and neutral excitons in InAs-Al0.6Ga0.4Asquantum dots. Physical Review B, 2002, 66, .	1.1	108
18	Quantum-confined Stark shifts of charged exciton complexes in quantum dots. Physical Review B, 2004, 70, .	1.1	108

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19	Intraband relaxation via polaron decay in InAs self-assembled quantum dots. Physical Review B, 2004, 70, .	1.1	101
20	Mode structure of the L3 photonic crystal cavity. Applied Physics Letters, 2007, 90, 241117.	1.5	99
21	Population Inversion in a Single InGaAs Quantum Dot Using the Method of Adiabatic Rapid Passage. Physical Review Letters, 2011, 106, 067401.	2.9	94
22	Enhanced phonon-assisted absorption in single InAs/GaAs quantum dots. Physical Review B, 2001, 63, .	1.1	90
23	InGaAsâˆ•AlAsSbâˆ•InP quantum cascade lasers operating at wavelengths close to 3Î¼m. Applied Physics Letters, 2007, 90, 021108.	1.5	89
24	p-doped 1.3Î¼m InAsâˆ•GaAs quantum-dot laser with a low threshold current density and high differential efficiency. Applied Physics Letters, 2006, 89, 073113.	1.5	87
25	Electric-field-dependent carrier capture and escape in self-assembled InAs/GaAs quantum dots. Applied Physics Letters, 2000, 77, 4344-4346.	1.5	86
26	Surface Band-Gap Narrowing in Quantized Electron Accumulation Layers. Physical Review Letters, 2010, 104, 256803.	2.9	86
27	Influences of the spacer layer growth temperature on multilayer InAsâˆ•GaAs quantum dot structures. Journal of Applied Physics, 2004, 96, 1988-1992.	1.1	85
28	Room-temperature 1.6Î¼m light emission from InAsâˆ•GaAs quantum dots with a thin GaAsSb cap layer. Journal of Applied Physics, 2006, 99, 046104.	1.1	85
29	Suppression of InAsâˆ•GaAs quantum dot decomposition by the incorporation of a GaAsSb capping layer. Applied Physics Letters, 2007, 90, 213105.	1.5	85
30	Photoluminescence, photoluminescence excitation, and resonant Raman spectroscopy of disordered and ordered Ga0.52In0.48P. Journal of Applied Physics, 1993, 73, 5163-5172.	1.1	81
31	Photocurrent spectroscopy of InAs/GaAs self-assembled quantum dots. Physical Review B, 2000, 62, 16784-16791.	1.1	80
32	Effect of thermal annealing and strain engineering on the fine structure of quantum dot excitons. Physical Review B, 2004, 70, .	1.1	78
33	Dynamics of Coherent and Incoherent Spin Polarizations in Ensembles of Quantum Dots. Physical Review Letters, 2004, 93, 057401.	2.9	76
34	Excess Avalanche Noise in $hbox{In}_{0.52}hbox{Al}_{0.48}hbox{As}$. IEEE Journal of Quantum Electronics, 2007, 43, 503-507.	1.0	75
35	Voltage enhancement in quantum well solar cells. Journal of Applied Physics, 1996, 80, 1201-1206.	1.1	73
36	Photoluminescence decay time measurements from self-organized InAs/GaAs quantum dots. Journal of Applied Physics, 1999, 86, 2555-2561.	1.1	73

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37	Optical transitions in type-II InAsâˆ•GaAs quantum dots covered by a GaAsSb strain-reducing layer. Applied Physics Letters, 2007, 91, .	1.5	73
38	Comparative study of InGaAs quantum dot lasers with different degrees of dot layer confinement. Applied Physics Letters, 2002, 81, 1-3.	1.5	72
39	Room-temperature broadband emission of an InGaAs/GaAs quantum dots laser. Optics Letters, 2007, 32, 44.	1.7	72
40	Element-sensitive measurement of the holeâ€“nuclear spin interaction in quantum dots. Nature Physics, 2013, 9, 74-78.	6.5	70
41	Avalanche Multiplication in InAlAs. IEEE Transactions on Electron Devices, 2007, 54, 11-16.	1.6	69
42	Filamentation and linewidth enhancement factor in InGaAs quantum dot lasers. Applied Physics Letters, 2002, 81, 3251-3253.	1.5	65
43	Systematic Study of the Effects of Modulation p-Doping on 1.3-$mu{hbox {m}}$ Quantum-Dot Lasers. IEEE Journal of Quantum Electronics, 2007, 43, 1129-1139.	1.0	65
44	Structural analysis of strained quantum dots using nuclear magnetic resonance. Nature Nanotechnology, 2012, 7, 646-650.	15.6	65
45	Electronic band structure of AlGaInP grown by solidâ€source molecularâ€beam epitaxy. Applied Physics Letters, 1994, 65, 213-215.	1.5	62
46	Individual neutral and chargedInxGa1âˆ’xAsâˆ’GaAsquantum dots with strong in-plane optical anisotropy. Physical Review B, 2005, 72, .	1.1	61
47	Excited states and selection rules in self-assembled InAs/GaAs quantum dots. Physical Review B, 1999, 60, R2185-R2188.	1.1	60
48	InGaAsâˆ•AlAsSb quantum cascade lasers. Applied Physics Letters, 2004, 85, 3992-3994.	1.5	60
49	Broad-band superluminescent light-emitting diodes incorporating quantum dots in compositionally modulated quantum wells. IEEE Photonics Technology Letters, 2006, 18, 58-60.	1.3	60
50	In situmonitoring of the surface reconstructions on InP(001) prepared by molecular beam epitaxy. Journal of Applied Physics, 1997, 82, 474-476.	1.1	59
51	Continuum transitions and phonon coupling in single self-assembled Stranski-Krastanow quantum dots. Physical Review B, 2003, 68, .	1.1	59
52	Magnetotunneling Spectroscopy of Dilute Ga(AsN) Quantum Wells. Physical Review Letters, 2003, 91, 126802.	2.9	59
53	Stacked low-growth-rate InAs quantum dots studied at the atomic level by cross-sectional scanning tunneling microscopy. Applied Physics Letters, 2003, 82, 3758-3760.	1.5	55
54	Î» âˆ¼ 3.1 â€, Î¼m room temperature InGaAs/AlAsSb/InP quantum cascade lasers. Applied Physics Letters, 2009, 94, .	1.5	55

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55	Suppression of nuclear spin bath fluctuations in self-assembled quantum dots induced by inhomogeneous strain. Nature Communications, 2015, 6, 6348.	5.8	54
56	Conductionâ€band discontinuity in InGaP/GaAs measured using both currentâ€voltage and photoemission methods. Applied Physics Letters, 1992, 60, 474-476.	1.5	53
57	Two-qubit conditional quantum-logic operation in a single self-assembled quantum dot. Physical Review B, 2008, 78, .	1.1	53
58	Photoluminescence spectroscopy of bandgap reduction in dilute InNAs alloys. Applied Physics Letters, 2005, 87, 182114.	1.5	52
59	The effect of p doping in InAs quantum dot lasers. Applied Physics Letters, 2006, 88, 111113.	1.5	52
60	Optical mode loss and gain of multiple-layer quantum-dot lasers. Applied Physics Letters, 2001, 78, 2629-2631.	1.5	50
61	Band gap of â€˜â€˜completely disorderedâ€™â€™ Ga0.52In0.48P. Applied Physics Letters, 1995, 66, 3185-3187.	1.5	48
62	Atomic scale study of the impact of the strain and composition of the capping layer on the formation of InAs quantum dots. Journal of Applied Physics, 2007, 101, 081707.	1.1	48
63	Thermodynamic balance in quantum dot lasers. Semiconductor Science and Technology, 2001, 16, 140-143.	1.0	47
64	Low threshold current density and negative characteristic temperature 1.3Î¼m InAs self-assembled quantum dot lasers. Applied Physics Letters, 2007, 90, 111102.	1.5	47
65	Quantum Dot Superluminescent Diodes for Optical Coherence Tomography: Device Engineering. IEEE Journal of Selected Topics in Quantum Electronics, 2010, 16, 1015-1022.	1.9	46
66	Structural analysis of life tested 1.3â€‚Î¼m quantum dot lasers. Journal of Applied Physics, 2008, 103, .	1.1	45
67	Improving optical properties of 1.55 Î¼m GaInNAs/GaAs multiple quantum wells with Ga(In)NAs barrier and space layer. Applied Physics Letters, 2003, 83, 4951-4953.	1.5	44
68	Temperature dependence of threshold current in p-doped quantum dot lasers. Applied Physics Letters, 2006, 89, 151118.	1.5	44
69	Carrier lifetimes in type-II InAs quantum dots capped with a GaAsSb strain reducing layer. Applied Physics Letters, 2008, 92, .	1.5	44
70	Beating of Exciton-Dressed States in a Single Semiconductor<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>InGaAs</mml:mi><mml:mo>/</mml:mo><mml:mi>GaAs</mml:mi></mml:math>Quantum Dot. Physical Review Letters, 2009, 102, 207401.	2.9	44
71	Optical orientation and control of spin memory in individual InGaAs quantum dots. Physical Review B, 2005, 72, .	1.1	43
72	Observation and Modeling of a Room-Temperature Negative Characteristic Temperature 1.3-mum p-Type Modulation-Doped Quantum-Dot Laser. IEEE Journal of Quantum Electronics, 2006, 42, 1259-1265.	1.0	43

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73	Magneto-optical studies of self-organized InAs/GaAs quantum dots. Physical Review B, 1998, 57, R2073-R2076.	1.1	42
74	Engineering carrier confinement potentials in 1.3-Î¼m InAs/GaAs quantum dots with InAlAs layers: Enhancement of the high-temperature photoluminescence intensity. Applied Physics Letters, 2003, 83, 3716-3718.	1.5	41
75	Polarized quantum dot emission from photonic crystal nanocavities studied under moderesonant enhanced excitation. Optics Express, 2007, 15, 17221.	1.7	41
76	Role of segregation in InAs/GaAs quantum dot structures capped with a GaAsSb strain-reduction layer. Physical Review B, 2009, 80, .	1.1	41
77	Breakup of the conduction band structure of diluteGaAs1âˆ’yNyalloys. Physical Review B, 2005, 71, .	1.1	40
78	Control of polarized single quantum dot emission in high-quality-factor microcavity pillars. Applied Physics Letters, 2006, 88, 051113.	1.5	40
79	Strongly coupled single quantum dot in a photonic crystal waveguide cavity. Applied Physics Letters, 2010, 97, 111101.	1.5	40
80	Allâ€solidâ€state subpicosecond passively mode locked erbiumâ€doped fiber laser. Applied Physics Letters, 1993, 63, 4-6.	1.5	39
81	Tuning the structural and optical properties of 1.3-Î¼m InAs/GaAs quantum dots by a combined InAlAs and GaAs strained buffer layer. Applied Physics Letters, 2003, 82, 3644-3646.	1.5	39
82	Vertical-geometry all-optical switches based on InAs/GaAs quantum dots in a cavity. Applied Physics Letters, 2009, 95, 021109.	1.5	39
83	Charge separation and temperature-induced carrier migration in Ga<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow /><mml:mrow><mml:mn>1</mml:mn><mml:mo>âˆ’</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub><in<mml:mrow xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow /><mml:mrow><mml:mn>1</mml:mn><mml:mo>âˆ’</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub><in</mml:mrow></mml:mrow>	1.1	39
84	Structural and optical studies of vertically aligned InAs/GaAs self-assembled quantum dots. Journal of Applied Physics, 2001, 90, 6374-6378.	1.1	38
85	Modal gain and internal optical mode loss of a quantum dot laser. Applied Physics Letters, 2000, 77, 163-165.	1.5	37
86	Whispering gallery resonances in semiconductor micropillars. Applied Physics Letters, 2007, 91, 071115.	1.5	37
87	Endochondral Growth Defect and Deployment of Transient Chondrocyte Behaviors Underlie Osteoarthritis Onset in a Natural Murine Model. Arthritis and Rheumatology, 2016, 68, 880-891.	2.9	37
88	Phase-matched second harmonic generation in asymmetric double quantum wells. Applied Physics Letters, 1998, 72, 2654-2656.	1.5	35
89	1.3â€…[micro sign]m InAs/GaAs quantum-dot laser with low-threshold current density and negative characteristic temperature above room temperature. Electronics Letters, 2006, 42, 922.	0.5	35
90	Photoluminescence of InNAs alloys: S-shaped temperature dependence and conduction-band nonparabolicity. Physical Review B, 2007, 76, .	1.1	35

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91	Energy level structure and electron relaxation times in InAsâˆ•InxGa1âˆ’xAs quantum dot-in-a-well structures. Applied Physics Letters, 2007, 91, 253502.	1.5	35
92	Passively mode-locked Er/sup 3+/ fiber laser using a semiconductor nonlinear mirror. IEEE Photonics Technology Letters, 1993, 5, 35-37.	1.3	34
93	Avalanche multiplication characteristics of Al/sub 0.8/Ga/sub 0.2/As diodes. IEEE Transactions on Electron Devices, 2001, 48, 2198-2204.	1.6	34
94	Gain in p-doped quantum dot lasers. Journal of Applied Physics, 2007, 101, 013107.	1.1	34
95	Nitrogen incorporation into strained (In, Ga) (As, N) thin films grown on (100), (511), (411), (311), and (111) GaAs substrates studied by photoreflectance spectroscopy and high-resolution x-ray diffraction. Journal of Applied Physics, 2006, 100, 093522.	1.1	33
96	Temperature-Dependent Gain and Threshold in P-Doped Quantum Dot Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2007, 13, 1261-1266.	1.9	33
97	P-type delta doping in silicon MBE. Thin Solid Films, 1990, 184, 15-19.	0.8	32
98	As/P exchange on InP(001) studied by reflectance anisotropy spectroscopy. Applied Physics Letters, 1997, 70, 1423-1425.	1.5	32
99	Intervalley scattering in GaAsâ€“AlAs quantum cascade lasers. Applied Physics Letters, 2002, 81, 1378-1380.	1.5	32
100	Raman scattering by LO phonon-plasmon coupled modes inn-typeIn0.53Ga0.47As. Physical Review B, 2001, 65, .	1.1	31
101	Defect states and commensurability in dual-periodAlxGa1âˆ’xAsphotonic crystal waveguides. Physical Review B, 2003, 68, .	1.1	31
102	Dilute nitride based double-barrier quantum-well infrared photodetector operating in the near infrared. Applied Physics Letters, 2003, 83, 3111-3113.	1.5	31
103	Comparison of intraband absorption and photocurrent in InAs/GaAs quantum dots. Applied Physics Letters, 2003, 83, 602-604.	1.5	31
104	Quantum Dot Superluminescent Diodes for Optical Coherence Tomography: Skin Imaging. IEEE Journal of Selected Topics in Quantum Electronics, 2010, 16, 748-754.	1.9	31
105	Core-level photoemission spectroscopy of nitrogen bonding in GaNxAs1âˆ’x alloys. Applied Physics Letters, 2004, 85, 1550-1552.	1.5	30
106	Observation of ultrahigh quality factor in a semiconductor microcavity. Applied Physics Letters, 2005, 86, 191109.	1.5	29
107	Crack formation in III-V epilayers grown under tensile strain on InP(001) substrates. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1996, 74, 383-393.	0.8	28
108	Strong in-plane polarized intraband absorption in vertically aligned InGaAs/GaAs quantum dots. Applied Physics Letters, 2003, 82, 3415-3417.	1.5	28

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109	Broad-Band Superluminescent Light Emitting Diodes Incorporating Quantum Dots in Compositionally Modulated Quantum Wells. Japanese Journal of Applied Physics, 2006, 45, 2542-2545.	0.8	28
110	Hypomorphic conditional deletion of E11/Podoplanin reveals a role in osteocyte dendrite elongation. Journal of Cellular Physiology, 2017, 232, 3006-3019.	2.0	28
111	Growth of strained InAs/InP quantum wells by molecular beam epitaxy. Applied Physics Letters, 1992, 60, 841-843.	1.5	26
112	Intraband magnetospectroscopy of singly and doubly chargedn-type self-assembled quantum dots. Physical Review B, 2006, 74, .	1.1	26
113	Thermal quenching of single localized excitons in GaInNAs layers. Applied Physics Letters, 2011, 98, .	1.5	26
114	Solidâ€source molecular beam epitaxy growth of GaInP and GaInPâ€containing quantum wells. Journal of Applied Physics, 1994, 75, 2029-2034.	1.1	25
115	Many-body effects in carrier capture and energy relaxation in self-organized InAs/GaAs quantum dots. Physica B: Condensed Matter, 1999, 272, 12-14.	1.3	25
116	Excess noise characteristics of Al/sub 0.8/Ga/sub 0.2/As avalanche photodiodes. IEEE Photonics Technology Letters, 2002, 14, 522-524.	1.3	25
117	The onset of plasticity in nanoscale contact loading. Proceedings of the Royal Society A: Mathematical, Physical and Engineering Sciences, 2003, 459, 2049-2068.	1.0	25
118	Direct observation of LO phonon-plasmon coupled modes in the infrared transmission spectra ofn-GaAs andnâˆ'InxGa1âˆ'xAsepilayers. Physical Review B, 2004, 69, .	1.1	25
119	Optical characteristics of 1.55Î¼m GaInNAs multiple quantum wells. Applied Physics Letters, 2004, 85, 4013-4015.	1.5	25
120	Investigation of carrier dynamics on InAs quantum dots embedded in InGaAsâ•GaAs quantum wells based on time-resolved pump and probe differential photoluminescence. Applied Physics Letters, 2006, 89, 181924.	1.5	25
121	Long nuclear spin polarization decay times controlled by optical pumping in individual quantum dots. Physical Review B, 2008, 77, .	1.1	25
122	Tuning Superluminescent Diode Characteristics for Optical Coherence Tomography Systems by Utilizing a Multicontact Device Incorporating Wavelength-Modulated Quantum Dots. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 757-763.	1.9	25
123	Quantum key distribution system in standard telecommunications fiber using a short wavelength single photon source. Journal of Applied Physics, 2010, 107, .	1.1	25
124	The effect of dead space on gain and excess noise in In0.48Ga0.52P pÂinÂdiodes. Semiconductor Science and Technology, 2003, 18, 803-806.	1.0	24
125	High Q modes in elliptical microcavity pillars. Applied Physics Letters, 2007, 90, 161105.	1.5	24
126	Carrier lifetimes in MBE and MOCVD InGaAs quantum wells. Semiconductor Science and Technology, 1993, 8, 307-309.	1.0	23

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127	Influence of composition on the piezoelectric effect and on the conduction band energy levels of InxGa1â^'xAsâ^•GaAs quantum dots. Journal of Applied Physics, 2004, 96, 5169-5172.	1.1	23
128	Siteâ€Controlled Singleâ€Photon Emitters Fabricated by Nearâ€Field Illumination. Advanced Materials, 2018, 30, e1705450.	11.1	23
129	Impact ionization coefficients in GaInPpâ€"iâ€"ndiodes. Applied Physics Letters, 1997, 70, 3567-3569.	1.5	22
130	Broadband 6Î¼m<Î»<8Î¼m superluminescent quantum cascade light-emitting diodes. Applied Physics Letters, 2006, 88, 121109.	1.5	22
131	Stark shift of the spectral response in quantum dots-in-a-well infrared photodetectors. Journal Physics D: Applied Physics, 2007, 40, 5537-5540.	1.3	22
132	All-optical switching in quantum cascade lasers. Applied Physics Letters, 2007, 90, 053505.	1.5	22
133	Effect of facet angle on effective facet reflectivity and operating characteristics of quantum dot edge emitting lasers and superluminescent light-emitting diodes. Applied Physics Letters, 2007, 91, 081112.	1.5	22
134	Intersublevel polaron dephasing in self-assembled quantum dots. Physical Review B, 2008, 77, .	1.1	22
135	Atomic scale high-angle annular dark field STEM analysis of the N configuration in dilute nitrides of GaAs. Physical Review B, 2009, 80, .	1.1	22
136	Temperature-dependent carrier tunneling for self-assembled InAs/GaAs quantum dots with a GaAsN quantum well injector. Applied Physics Letters, 2010, 96, 151104.	1.5	22
137	Effects of intermixing on modulation p-doped quantum dot superluminescent light emitting diodes. Optics Express, 2010, 18, 7055.	1.7	22
138	General characteristics of crack arrays in epilayers grown under tensile strain. Semiconductor Science and Technology, 2000, 15, 325-330.	1.0	21
139	Impact ionization coefficients of Al0.8Ga0.2As. Applied Physics Letters, 2000, 77, 4374-4376.	1.5	21
140	1.3 Î¼m lasers with AlInAs-capped self-assembled quantum dots. Applied Physics Letters, 2003, 83, 4710-4712.	1.5	21
141	Mapping quantum dot-in-well structures on the nanoscale using the plasmon peak in electron energy loss spectra. Physical Review B, 2005, 72, .	1.1	21
142	Mechanism for improvements of optical properties of 1.3-Î¼m InAsâ^•GaAs quantum dots by a combined InAlAsâ€"InGaAs cap layer. Journal of Applied Physics, 2005, 98, 083516.	1.1	21
143	Long wavelength bulk GaInNAs pâ^'iâ^'n photodiodes lattice matched to GaAs. Journal of Applied Physics, 2007, 101, 064506.	1.1	21
144	Splitting and lasing of whispering gallery modes in quantum dot micropillars. Optics Express, 2010, 18, 22578.	1.7	21

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145	Avalanche multiplication and breakdown in Ga/sub 0.52/In/sub 0.48/P diodes. IEEE Transactions on Electron Devices, 1998, 45, 2096-2101.	1.6	20
146	Temperature dependence of the lasing wavelength of InGaAs quantum dot lasers. Journal of Applied Physics, 2001, 90, 4859-4861.	1.1	20
147	Temperature dependence of avalanche multiplication in submicron Al0.6Ga0.4As diodes. Journal of Applied Physics, 2002, 92, 7684-7686.	1.1	20
148	Determination of the outward relaxation of cleaved strained InAs structures by scanning tunneling microscopy. Applied Surface Science, 2002, 190, 258-263.	3.1	20
149	Influence of growth temperature on the structural and optical quality of GaInNAs/GaAs multi-quantum wells. Semiconductor Science and Technology, 2004, 19, 813-818.	1.0	20
150	Î»â¯¼4â€“5.3â€‰Î¼m intersubband emission from InGaAsâ€“AlAsSb quantum cascade structures. Applied Physics Letters, 2004, 84, 1447-1449.	1.5	20
151	Effect of hydrostatic pressure on the fragmented conduction band structure of dilute Ga(AsN) alloys. Physical Review B, 2005, 72, .	1.1	20
152	The role of high growth temperature GaAs spacer layers in 1.3-/spl mu/m In(Ga)As quantum-dot lasers. IEEE Photonics Technology Letters, 2005, 17, 2011-2013.	1.3	20
153	Fabrication of InAs photodiodes with reduced surface leakage current. Proceedings of SPIE, 2007, 6740, 51.	0.8	20
154	Tuning the photoresponse of quantum dot infrared photodetectors across the 8â€“12Î¼m atmospheric window via rapid thermal annealing. Applied Physics Letters, 2007, 91, 143502.	1.5	20
155	Structural properties of GaAsNâˆ•GaAs quantum wells studied at the atomic scale by cross-sectional scanning tunneling microscopy. Applied Physics Letters, 2008, 93, 083103.	1.5	20
156	Electrical control of fine-structure splitting in self-assembled quantum dots for entangled photon pair creation. Applied Physics Letters, 2010, 97, .	1.5	20
157	Observation of phase shifts in a vertical cavity quantum dot switch. Applied Physics Letters, 2011, 98, 231101.	1.5	20
158	Microstructure and cathodoluminescence of MBE-grown (001) InxGa1-xP/GaAs strained-layer heterostructures. Semiconductor Science and Technology, 1993, 8, 502-508.	1.0	19
159	Coherency Strain as an Athermal Strengthening Mechanism. Physical Review Letters, 1997, 78, 3912-3914.	2.9	19
160	Gain characteristics of InAs/GaAs self-organized quantum-dot lasers. Applied Physics Letters, 1999, 75, 3512-3514.	1.5	19
161	Decreasing the emission wavelength of GaAsâ€“AlGaAs quantum cascade lasers by the incorporation of ultrathin InGaAs layers. Applied Physics Letters, 2001, 78, 413-415.	1.5	19
162	Room-temperature operation of an InAsâ€“GaAsâ€“AlAs quantum-cascade laser. Applied Physics Letters, 2003, 82, 3409-3411.	1.5	19

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163	Structural studies of a combined InAlAsâ€“InGaAs capping layer on 1.3-Î¼m Inas/GaAs quantum dots. Journal of Crystal Growth, 2005, 285, 17-23.	0.7	19
164	Effects of alloy intermixing on the lateral confinement potential in InAsâˆ•GaAs self-assembled quantum dots probed by intersublevel absorption spectroscopy. Applied Physics Letters, 2007, 90, 163107.	1.5	19
165	Origin of Temperature-Dependent Threshold Current in p-Doped and Undoped In(Ga)As Quantum Dot Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2008, 14, 1162-1170.	1.9	19
166	Enhanced nonradiative Auger recombination in p-type modulation doped InAs/GaAs quantum dots. Applied Physics Letters, 2008, 93, .	1.5	19
167	Electrical, optical and luminescence properties of a-Si/SiN multilayers. Journal of Non-Crystalline Solids, 1985, 77-78, 1081-1084.	1.5	18
168	Optical spectroscopy of AlGaInP based wide band gap quantum wells. Superlattices and Microstructures, 1994, 15, 313.	1.4	18
169	Modal gain and lasing states in InAs/GaAs self-organized quantum dot lasers. Journal of Applied Physics, 2000, 87, 615-617.	1.1	18
170	On the diffusion of lattice matched InGaAs/InP microstructures. Journal of Applied Physics, 2003, 93, 3881-3885.	1.1	18
171	Temperature-induced carrier escape processes studied in absorption of individualInxGa1âˆ’xAsquantum dots. Physical Review B, 2004, 69, .	1.1	18
172	Design, growth, fabrication, and characterization of InAsâˆ•GaAs 1.3Î¼m quantum dot broadband superluminescent light emitting diode. Journal of Applied Physics, 2006, 100, 103105.	1.1	18
173	Role of elastic anisotropy in the vertical alignment of In(Ga)As quantum dot superlattices. Applied Physics Letters, 2006, 88, 193118.	1.5	18
174	Enhanced room-temperature quantum-dot effects in modulation-doped InAs/GaAs quantum dots. Applied Physics Letters, 2009, 95, 171902.	1.5	18
175	Theoretical and experimental investigations of the temperature dependent continuous wave lasing characteristics and the switch-on dynamics of an InAs/InGaAs quantum-dot semiconductor laser. Optics Communications, 2010, 283, 5092-5098.	1.0	18
176	Reverse-emission-state-transition mode locking of a two-section InAs/InGaAs quantum dot laser. Applied Physics Letters, 2010, 97, .	1.5	18
177	From the artificial atom to the Kondo-Anderson model: Orientation-dependent magnetophotoluminescence of charged excitons in InAs quantum dots. Physical Review B, 2013, 87, .	1.1	18
178	Recombination in a-Si:H Based Materials: Evidence for Two Slow Radiative Processes. , 1987, , 357-368.		18
179	Carrier dynamics in short wavelength self-assembled InAs/Al0.6Ga0.4As quantum dots with indirect barriers. Journal of Applied Physics, 2003, 93, 3524-3528.	1.1	17
180	InGaAsâˆ•AlAsSbâˆ•InP strain compensated quantum cascade lasers. Applied Physics Letters, 2007, 90, 151105.	1.5	17

#	Article	IF	Citations
181	Two photon absorption in quantum dot-in-a-well infrared photodetectors. Applied Physics Letters, 2008, 92, 023501.	1.5	17
182	Electron coherence length and mobility in highly mismatched III-N-V alloys. Applied Physics Letters, 2008, 93, .	1.5	17
183	Multi-section quantum dot superluminescent diodes for spectral shape engineering. IET Optoelectronics, 2009, 3, 100-104.	1.8	17
184	IIIâ€“V semiconductor devices integrated with silicon. Semiconductor Science and Technology, 2013, 28, 090301.	1.0	17
185	Precise Arrays of Epitaxial Quantum Dots Nucleated by In Situ Laser Interference for Quantum Information Technology Applications. ACS Applied Nano Materials, 2020, 3, 4739-4746.	2.4	17
186	GaInPâ€“AlGaInP band offsets determined from hydrostatic pressure measurements. Applied Physics Letters, 1995, 66, 619-621.	1.5	16
187	Photoluminescence spectroscopy of intersubband population inversion in aGaAs/AlxGa1â^'xAstriple-barrier tunneling structure. Physical Review B, 1998, 57, 6290-6293.	1.1	16
188	Electronic properties of InAs/GaAs self-assembled quantum dots studied by photocurrent spectroscopy. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 9, 106-113.	1.3	16
189	Measurements of optical losses in mid-infrared semiconductor lasers using Fabryâ€“PÃ©rot transmission oscillations. Journal of Applied Physics, 2004, 95, 7584-7587.	1.1	16
190	Recombination mechanisms in 1.3-/spl mu/m InAs quantum-dot lasers. IEEE Photonics Technology Letters, 2006, 18, 965-967.	1.3	16
191	Single photon sources based upon single quantum dots in semiconductor microcavity pillars. Journal of Modern Optics, 2007, 54, 453-465.	0.6	16
192	Correlation between defect density and current leakage in InAsâ•GaAs quantum dot-in-well structures. Journal of Applied Physics, 2009, 106, .	1.1	16
193	State-switched modelocking of two-segment quantum dot laser via self-electro-optical quantum dot absorber. Electronics Letters, 2010, 46, 161.	0.5	16
194	Dynamic nuclear polarization in InGaAs/GaAs and GaAs/AlGaAs quantum dots under nonresonant ultralow-power optical excitation. Physical Review B, 2013, 88, .	1.1	16
195	Few-second-long correlation times in a quantum dot nuclear spin bath probed by frequency-comb nuclear magnetic resonance spectroscopy. Nature Physics, 2016, 12, 688-693.	6.5	16
196	Strained layer (111)B GaAs/InGaAs single quantum well lasers and the dependence of their characteristics upon indium composition. Journal of Applied Physics, 2001, 89, 4689-4696.	1.1	15
197	Avalanche multiplication and breakdown Al/sub x/Ga/sub 1-x/(x > 0.9). IEEE Transactions on Electron Devices, 2002, 49, 2349-2351.	1.6	15
198	Surface elemental segregation and the Stranskiâ€“Krastanow epitaxial islanding transition. Applied Surface Science, 2005, 244, 65-70.	3.1	15

#	Article	IF	Citations
199	Growth, Fabrication, and Operating Characteristics of Ultra-Low Threshold Current Density 1.3 Âµm Quantum Dot Lasers. Japanese Journal of Applied Physics, 2005, 44, 2520-2522.	0.8	15
200	Measurement of modal absorption, gain and recombination in p-doped and intrinsic quantum dot structures. IEE Proceedings: Optoelectronics, 2006, 153, 316-320.	0.8	15
201	Effects of growth temperature on the structural and optical properties of 1.6Î¼m GaInNAsâ•GaAs multiple quantum wells. Applied Physics Letters, 2006, 88, 191907.	1.5	15
202	Coherent response of a quantum dot exciton driven by a rectangular spectrum optical pulse. Physical Review B, 2007, 75, .	1.1	15
203	Improved performance of In0.6Ga0.4Asâ•AlAs0.67Sb0.33â•InP quantum cascade lasers by introduction of AlAs barriers in the active regions. Applied Physics Letters, 2007, 91, 051123.	1.5	15
204	High-Power and Broadband Quantum Dot Superluminescent Diodes Centered at 1250 nm for Optical Coherence Tomography. IEEE Journal of Selected Topics in Quantum Electronics, 2007, 13, 1267-1272.	1.9	15
205	Electrical properties of nitrogen-related defects in n-type GaAsN grown by molecular-beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 2652-2654.	0.8	15
206	High performance intermixed p-doped quantum dot superluminescent diodes at 1.2â€…[micro sign]m. Electronics Letters, 2010, 46, 295.	0.5	15
207	GaInNAs-based Hellish-vertical cavity semiconductor optical amplifier for 1.3 Î¼m operation. Nanoscale Research Letters, 2011, 6, 104.	3.1	15
208	Pulse control protocols for preserving coherence in dipolar-coupled nuclear spin baths. Nature Communications, 2019, 10, 3157.	5.8	15
209	Broadband, wide-angle antireflection in GaAs through surface nano-structuring for solar cell applications. Scientific Reports, 2020, 10, 6269.	1.6	15
210	Measurement of the direct energy gap ofAl0.5In0.5P: Implications for the band discontinuity atGa1â’xInxP/AlyIn1â’yP heterojunctions. Physical Review B, 1994, 50, 11190-11191.	1.1	14
211	Growth of InAsxP1â’x/InP multiâ€quantum well structures by solid source molecular beam epitaxy. Journal of Applied Physics, 1995, 78, 3330-3334.	1.1	14
212	Effect of the electron population on intraband absorption in InAs/GaAs self-assembled quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 105-109.	1.3	14
213	Composition modulation in GaInNAs quantum wells: Comparison of experiment and theory. Journal of Applied Physics, 2005, 97, 073705.	1.1	14
214	1.34â€…[micro sign]m GaInNAs quantum well lasers with low room-temperature threshold current density. Electronics Letters, 2006, 42, 923.	0.5	14
215	Control of polarization and mode mapping of small volume high Q micropillars. Journal of Applied Physics, 2007, 102, 043105.	1.1	14
216	Detailed Design and Characterization of All-Optical Switches Based on InAs/GaAs Quantum Dots in a Vertical Cavity. IEEE Journal of Quantum Electronics, 2010, 46, 1582-1589.	1.0	14

#	Article	IF	Citations
217	Laser Location and Manipulation of a Single Quantum Tunneling Channel in an InAs Quantum Dot. Physical Review Letters, 2012, 108, 117402.	2.9	14
218	Polariton states bound to defects in GaAs/AlAs planar microcavities. Physical Review B, 2012, 85, .	1.1	14
219	Broadband enhancement of light-matter interaction in photonic crystal cavities integrating site-controlled quantum dots. Physical Review B, 2020, 101, .	1.1	14
220	Optical spectroscopic observation of spontaneous long range ordering in AlGaInP. Applied Physics Letters, 1996, 68, 3266-3268.	1.5	13
221	Light sources for wavelengths > 2 Âµm grown by MBE on InP using a strain relaxed buffer. IEE Proceedings: Optoelectronics, 1998, 145, 292-296.	0.8	13
222	Filamentation and linewidth enhancement factor In InGaAs quantum dot lasers. , 2001, , .		13
223	Laser dynamics in self-pulsating quantum dot systems. Journal of Applied Physics, 2004, 95, 1036-1041.	1.1	13
224	Polaron relaxation dynamics in InAs/GaAs self-assembled quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 405-408.	1.3	13
225	Anisotropy of the electron energy levels in InxGa1âˆ’xAs/GaAs quantum dots with non uniform composition. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 436-440.	1.3	13
226	Effects of photon and thermal coupling mechanisms on the characteristics of self-assembled<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi mathvariant="normal">In</mml:mi><mml:mi mathvariant="normal">As</mml:mi><mml:mo>âˆ•</mml:mo><mml:mi mathvariant="normal">Ga</mml:mi><mml:mi mathvariant="normal">As</mml:mi></mml:mrow></mml:math>quantum dot lasers. Physical Review B,	1.1	13
227	Broadband quantum cascade laser emitting from 7.7to8.4Î¼m operating up to 340K. Journal of Applied Physics, 2007, 101, 046103.	1.1	13
228	Nuclear spin pumping under resonant optical excitation in a quantum dot. Applied Physics Letters, 2008, 93, 073113.	1.5	13
229	Electron effective mass and Si-donor binding energy inGaAs1âˆ’xNxprobed by a high magnetic field. Physical Review B, 2008, 77, .	1.1	13
230	Maximising performance of optical coherence tomography systems using a multi-section chirped quantum dot superluminescent diode. Microelectronics Journal, 2009, 40, 588-591.	1.1	13
231	Optical properties of single charge tuneable InGaAs quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 127-130.	1.3	12
232	Dynamics of the wetting-Layer-quantum-dot interaction in InGaAs self-assembled systems. IEEE Journal of Quantum Electronics, 2005, 41, 344-350.	1.0	12
233	All semiconductor swept laser source utilizing quantum dots. Applied Physics Letters, 2007, 91, 121119.	1.5	12
234	Magnetophonon oscillations in the negative differential conductance of dilute nitrideGaAs1âˆ’xNxsubmicron diodes. Physical Review B, 2007, 75, .	1.1	12

#	Article	IF	Citations
235	Zero and Controllable Linewidth Enhancement Factor in p-Doped 1.3 Âµm Quantum Dot Lasers. Japanese Journal of Applied Physics, 2007, 46, 2421-2423.	0.8	12
236	Dual-State Absorber-Photocurrent Characteristics and Bistability of Two-Section Quantum-Dot Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 1-9.	1.9	12
237	A comparison of photo- and electroluminescence in a-Si p-i-n junctions. Journal of Non-Crystalline Solids, 1985, 77-78, 695-698.	1.5	11
238	Optical bistability in an InGaAs/InP multiple quantum well waveguide Fabryâ€“Perot cavity. Applied Physics Letters, 1993, 63, 1610-1612.	1.5	11
239	Reflectance anisotropy spectroscopy study of the surface reconstructions of decapped InP(001). Journal of Applied Physics, 1998, 83, 480-485.	1.1	11
240	Cracking self-assembled InAs quantum dots. Applied Physics A: Materials Science and Processing, 2001, 72, S205-S207.	1.1	11
241	Composition profiling at the atomic scale in IIIâ€“V nanostructures by cross-sectional STM. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 526-532.	1.3	11
242	Multiplication and excess noise in AlxGa1â^'xAs/GaAs multilayer avalanche photodiodes. Journal of Applied Physics, 2003, 94, 2631-2637.	1.1	11
243	Effect of the growth parameters on the structure and morphology of InAs/InGaAs/GaAs DWELL quantum dot structures. Journal of Crystal Growth, 2005, 278, 151-155.	0.7	11
244	Intra-valence band transitions in self-assembled InAsâ•GaAs quantum dots studied using photocurrent spectroscopy. Journal of Applied Physics, 2006, 100, 013106.	1.1	11
245	Two step optimized process for scanning tunneling microscopy tip fabrication. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, 371-375.	0.6	11
246	Deep levels in H-irradiated GaAs1-xNx (xâ€‰<â€‰0.01) grown by molecular beam epitaxy. Journal of Applied Physics, 2011, 110, .	1.1	11
247	InxGa1â^'xAs/InP quantum well structures grown on [111]B InP. Microelectronics Journal, 1995, 26, 805-810.	1.1	10
248	Conduction band discontinuities in Ga0.5In0.5Pâ€AlxGa0.5â^'xIn0.5P heterojunctions measured by internal photoemission. Applied Physics Letters, 1995, 66, 2852-2854.	1.5	10
249	Optical properties of (AlxGa1â^'x)0.52In0.48P at the crossover from a direct-gap to an indirect-gap semiconductor. Journal of Applied Physics, 1998, 83, 2241-2249.	1.1	10
250	Indium segregation in (111)B GaAs-InxGa1-xAs quantum wells determined by transmission electron microscopy. Journal Physics D: Applied Physics, 2001, 34, 1943-1946.	1.3	10
251	Spatially resolved scanning tunneling luminescence on self-assembled InGaAs/GaAs quantum dots. Applied Physics Letters, 2003, 83, 290-292.	1.5	10
252	Strain interactions and defect formation in stacked InGaAs quantum dot and dot-in-well structures. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 245-251.	1.3	10

#	Article	IF	Citations
253	Optimizing the growth of 1.3-Î¼m InAs/InGaAs dots-in-a-well structure: Achievement of high-performance laser. Materials Science and Engineering C, 2005, 25, 779-783.	3.8	10
254	Singlet and triplet polaron relaxation in doubly charged self-assembled quantum dots. New Journal of Physics, 2007, 9, 259-259.	1.2	10
255	Optical phonon behavior in strain-free dilute Ga(As,N) studied by Raman scattering. Journal of Applied Physics, 2007, 102, 013502.	1.1	10
256	Photonic crystal nanocavities in GaAs/AlGaAs with oxidised bottom cladding. Photonics and Nanostructures - Fundamentals and Applications, 2013, 11, 139-144.	1.0	10
257	A lithographic approach for quantum dot-photonic crystal nanocavity coupling in dilute nitrides. Microelectronic Engineering, 2017, 174, 16-19.	1.1	10
258	Highly doped 1.55 Âµm GaxIn1-xAs/InP distributed Bragg reflector stacks. Electronics Letters, 1994, 30, 1526-1527.	0.5	9
259	Electroabsorption modulation in strained piezoelectric InGaAs/InP multiquantum wells operating at Î» â‰ƒ 1.55 Âµm. Electronics Letters, 1994, 30, 1707-1708.	0.5	9
260	Electron spectroscopy of dilute nitrides. Journal of Physics Condensed Matter, 2004, 16, S3201-S3214.	0.7	9
261	Improved temperature performance of 1.31-/spl mu/m quantum dot lasers by optimized ridge waveguide design. IEEE Photonics Technology Letters, 2005, 17, 1785-1787.	1.3	9
262	Integration of a resonant tunneling diode and an optical communications laser. IEEE Photonics Technology Letters, 2006, 18, 1518-1520.	1.3	9
263	Photoluminescence beyond 1.5Î¼m from InAs quantum dots. Microelectronics Journal, 2006, 37, 1468-1470.	1.1	9
264	Strong Effect of Resonant Impurities on Landau-Level Quantization. Physical Review Letters, 2006, 96, 236802.	2.9	9
265	High-Power 1.3-mum Quantum-Dot Superluminescent Light-Emitting Diode Grown by Molecular Beam Epitaxy. IEEE Photonics Technology Letters, 2007, 19, 109-111.	1.3	9
266	GaInNAs(Sb) surface normal devices. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 85-92.	0.8	9
267	Quantum dot dipole orientation and excitation efficiency of micropillar modes. Optics Express, 2008, 16, 19201.	1.7	9
268	Simple theoretical model for the temperature stability of InAs/GaAs self-assembled quantum dot lasers with different p-type modulation doping levels. Applied Physics Letters, 2008, 93, 161103.	1.5	9
269	Dependence of the Electroluminescence on the Spacer Layer Growth Temperature of Multilayer Quantum-Dot Laser Structures. IEEE Journal of Quantum Electronics, 2009, 45, 79-85.	1.0	9
270	Terahertz activated luminescence of trapped carriers in InGaAs/GaAs quantum dots. Applied Physics Letters, 2010, 97, 031101.	1.5	9

#	Article	IF	Citations
271	Reverse ground-state excited-state transition dynamics in two-section quantum dot semiconductor lasers: mode-locking and state-switching. Proceedings of SPIE, 2010, , .	0.8	9
272	How to best measure atomic segregation to grain boundaries by analytical transmission electron microscopy. Journal of Materials Science, 2014, 49, 3898-3908.	1.7	9
273	Direct patterning of periodic semiconductor nanostructures using single-pulse nanosecond laser interference. Optics Express, 2020, 28, 32529.	1.7	9
274	Study of a backgated metalâ€semiconductorâ€metal photodetector. Applied Physics Letters, 1996, 68, 815-817.	1.5	8
275	Mid-infrared intersubband electroluminescence from a single-period GaAs/AlGaAs triple barrier structure. Applied Physics Letters, 1998, 72, 2141-2143.	1.5	8
276	Electronic structure of InAsâ€“GaAs self-assembled quantum dots studied by perturbation spectroscopy. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 6, 348-357.	1.3	8
277	= 8.3 [micro sign]m GaAs/AlAs quantum cascade lasers incorporating InAs monolayers. Electronics Letters, 2001, 37, 1292.	0.5	8
278	Room temperature GaAs-based quantum cascade laser with GaInP waveguide cladding. Electronics Letters, 2002, 38, 1539.	0.5	8
279	Mode formation in broad area quantum dot lasers at 1060 nm. Optics Communications, 2004, 235, 387-393.	1.0	8
280	Structural and optical quality of InGaAsN quantum wells grown on misoriented GaAs (111)b substrates by molecular beam epitaxy. Journal of Crystal Growth, 2004, 270, 62-68.	0.7	8
281	Polaron relaxation channel in InAs/GaAs self-assembled quantum dots. Semiconductor Science and Technology, 2004, 19, S316-S318.	1.0	8
282	Concentration dependent interdiffusion in InGaAsâˆ•GaAs as evidenced by high resolution x-ray diffraction and photoluminescence spectroscopy. Journal of Applied Physics, 2005, 97, 013536.	1.1	8
283	Improved performance of 1.3-/spl mu/m In(Ga)As quantum-dot lasers by modifying the temperature profile of the GaAs spacer layers. IEEE Photonics Technology Letters, 2006, 18, 1557-1559.	1.3	8
284	Infrared modulated interlevel spectroscopy of 1.3Î¼m self-assembled quantum dot lasers using a free electron laser. Applied Physics Letters, 2006, 88, 081108.	1.5	8
285	Focused ion beam etching for the fabrication of micropillar microcavities made of III-V semiconductor materials. Journal of Vacuum Science & Technology B, 2007, 25, 1197.	1.3	8
286	The evolution of Ga and As core levels in the formation of Feâˆ•GaAs (001): A high resolution soft x-ray photoelectron spectroscopic study. Journal of Applied Physics, 2008, 104, .	1.1	8
287	Cryogenic confocal microscopy with rotation in a magnetic field. Review of Scientific Instruments, 2010, 81, 013906.	0.6	8
288	Asymmetric characteristics of InGaP/GaAs double-heterojunction bipolar transistors grown by solid source molecular beam epitaxy. Semiconductor Science and Technology, 1992, 7, 425-428.	1.0	7

#	Article	IF	Citations
289	High reflectivity and low resistance 1.55Î¼m Al0.65In0.35As/Ga0.63In0.37As strained quarter wave Bragg reflector stack. Electronics Letters, 1993, 29, 1947.	0.5	7
290	Surface structure of InP(001) under dynamic and static conditions of molecular beam epitaxy. Applied Surface Science, 1998, 123-124, 313-318.	3.1	7
291	Comparison of performance of GaAs-AlGaAs and InGaAs-AlInAs quantum cascade lasers. Electronics Letters, 1999, 35, 2034.	0.5	7
292	Excited States in Self-Assembled InAs/GaAs Quantum Dots under High Pressure. Physica Status Solidi (B): Basic Research, 1999, 211, 73-77.	0.7	7
293	Quantum Confined Stark Effect and Permanent Dipole Moment of InAsâ€“GaAs Self-Assembled Quantum Dots. Physica Status Solidi A, 2000, 178, 269-275.	1.7	7
294	Strain relaxation behavior of InxGa1âˆ’xAs quantum wells on vicinal GaAs (111)B substrates. Applied Physics Letters, 2002, 80, 1541-1543.	1.5	7
295	Precise measurement of the fraction of charged dots in self-assembled quantum dot ensembles using ultrafast pump-probe techniques. Applied Physics Letters, 2004, 85, 2226-2228.	1.5	7
296	RF-plasma source qualification and compositional characterisation of GaNAs superlattices using SIMS. Applied Surface Science, 2006, 252, 7218-7220.	3.1	7
297	High-performance 1.3â€…Âµm InAs/GaAs quantum-dot lasers with low threshold current and negative characteristic temperature. IEE Proceedings: Optoelectronics, 2006, 153, 280-283.	0.8	7
298	Modifying the electronic properties of GaAsâˆ•AlAs superlattices with low-density nitrogen doping. Journal of Applied Physics, 2006, 100, 063718.	1.1	7
299	Coherent near-infrared wavelength conversion in semiconductor quantum cascade lasers. Applied Physics Letters, 2006, 89, 183507.	1.5	7
300	Molecular Beam Epitaxial Growth of High Power Quantum Dot Super-Luminecent Diodes. Japanese Journal of Applied Physics, 2007, 46, 2418-2420.	0.8	7
301	Nonradiative Recombination in Multiple Layer In(Ga)As Quantum-Dot Lasers. IEEE Journal of Quantum Electronics, 2007, 43, 698-703.	1.0	7
302	Effect of Dead Space on Low-Field Avalanche Multiplication in InP. IEEE Transactions on Electron Devices, 2007, 54, 2051-2054.	1.6	7
303	Structure of InAs quantum dots-in-a-well nanostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1988-1990.	1.3	7
304	High field electron dynamics in dilute nitride Ga(AsN). Applied Physics Letters, 2008, 93, .	1.5	7
305	Limits of In(Ga)As/GaAs quantum dot growth. Physica Status Solidi (B): Basic Research, 2009, 246, 717-720.	0.7	7
306	Coherence function control of Quantum Dot Superluminescent Light Emitting Diodes by frequency selective optical feedback. Optics Express, 2009, 17, 13365.	1.7	7

#	Article	IF	Citations
307	Temperature dependence of Ga-assisted oxide desorption on GaAs(001). Journal of Physics: Conference Series, 2010, 209, 012066.	0.3	7
308	Electrical modulation of the optical properties of mid-infrared metamaterials. Applied Physics Letters, 2012, 101, 251109.	1.5	7
309	In-plane interdot carrier transfer in InAs/GaAs quantum dots. Applied Physics Letters, 2012, 100, 152101.	1.5	7
310	Ordered GaAs quantum dots by droplet epitaxy using in situ direct laser interference patterning. Applied Physics Letters, 2021, 118, .	1.5	7
311	Observation of Wannier-Stark ladder transitions inInxGa1âˆ'xAs-GaAs piezoelectric superlattices. Physical Review B, 1995, 52, R14340-R14343.	1.1	6
312	Lowâ€temperature mobility of twoâ€dimensional electrons in (Ga,In)Asâ€"(Al,In)As heterojunctions. Journal of Applied Physics, 1996, 79, 8465-8469.	1.1	6
313	Dynamical Band Gap Renormalization in Self-Organized InAs/GaAs Quantum Dots. Physica Status Solidi A, 2000, 178, 345-348.	1.7	6
314	Static and growing InP and InAs surfaces: reflection-anisotropy spectroscopy under the conditions of solid-source MBE. Thin Solid Films, 2000, 364, 6-11.	0.8	6
315	Photocurrent spectroscopy of InAs/GaAs self-assembled quantum dots: observation of a permanent dipole moment. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 408-412.	1.3	6
316	Photocurrent Spectroscopy of InAs/GaAs Self-Assembled Quantum Dots. Physica Status Solidi (B): Basic Research, 2001, 224, 497-502.	0.7	6
317	Performance of lasers containing three, five and seven layers of quantum dots. IEE Proceedings: Optoelectronics, 2001, 148, 238-242.	0.8	6
318	Characterisation of strained (111)B InGaAs/GaAs quantum well lasers with intracavity optical modulator. Microelectronics Journal, 2002, 33, 547-552.	1.1	6
319	Demonstration of a blueshift in type II asymmetric InP/InAsP/InGaAs multiple quantum wells. Journal of Applied Physics, 2003, 94, 3222-3228.	1.1	6
320	Lasing and spontaneous emission characteristics of 1.3Î¼m In(Ga)As quantum-dot lasers. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 382-385.	1.3	6
321	Anomalous Stark shifts in single vertically coupled pairs of InGaAs quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 302-307.	1.3	6
322	Structural and optical properties of high In and N content GaInNAs quantum wells. Thin Solid Films, 2005, 483, 185-190.	0.8	6
323	Observation of a low Curie temperature ferromagnetic phase of ultrathin epitaxial Fe films on GaAs(001). Journal of Magnetism and Magnetic Materials, 2005, 292, 241-247.	1.0	6
324	Unfaulting of dislocation loops in the GaInNAs alloy: An estimation of the stacking fault energy. Journal of Applied Physics, 2005, 98, 023521.	1.1	6

#	Article	IF	Citations
325	Exciton fine structure splitting in dot-in-a-well structures. Applied Physics Letters, 2006, 88, 131115.	1.5	6
326	Polarisation control and emission enhancement of a quantum dot in ultra-high finesse microcavity pillars. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 500-503.	1.3	6
327	High performance 1.3Î¼m InAs/GaAs quantum dot lasers with low threshold current and negative characteristic temperature. , 2006, 6184, 374.		6
328	Broadband quantum dot superluminescent LED with angled facet formed by focused ion beam etching. Electronics Letters, 2007, 43, 587.	0.5	6
329	Quantum Well and Dot Self-Aligned Stripe Lasers Utilizing an InGaP Optoelectronic Confinement Layer. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 819-827.	1.9	6
330	Dilute (In,Ga)(As,N) thin films grown by molecular beam epitaxy on (100) and non-(100) GaAs substrates: a Raman-scattering study. Journal of Materials Science: Materials in Electronics, 2009, 20, 116-119.	1.1	6
331	InAs/GaAs(001) wetting layer formation observed in situ by concurrent MBE and STM. Surface Science, 2009, 603, 3439-3444.	0.8	6
332	Micro-photoluminescence of GaInNAs layers grown on GaAs substrates of various crystallographic orientations. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1655-1658.	0.8	6
333	Formation of laterally ordered quantum dot molecules by in situ nanosecond laser interference. Applied Physics Letters, 2020, 116, .	1.5	6
334	Growth and in vivo STM of III-V Compound Semiconductors. Springer Proceedings in Physics, 2008, , 471-476.	0.1	6
335	Conditional deletion of E11/Podoplanin in bone protects against ovariectomy-induced increases in osteoclast formation and activity. Bioscience Reports, 2020, 40, .	1.1	6
336	Particulate contamination in silicon grown by molecular-beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1990, 8, 21.	1.6	5
337	On the low-temperature efficiency of photoluminescence in a-Si: H and other materials. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1991, 63, 179-191.	0.6	5
338	Guided-wave measurements of real-excitation optical nonlinearities in a tensile strained InGaAs on InP quantum well at 1.5 Î¼m. Optics Communications, 1993, 102, 473-477.	1.0	5
339	Submilliwatt optical bistability in a coated InGaAs/InP multiquantum well waveguide Fabryâ€“Perot cavity. Electronics Letters, 1993, 29, 1537.	0.5	5
340	Avalanche breakdown in (AlxGa1-x)0.52In0.48P pin junctions. Electronics Letters, 1994, 30, 907.	0.5	5
341	Carrier lifetime and exciton saturation in a strain-balanced InGaAs/InAsP multiple quantum well. Journal of Applied Physics, 1998, 83, 306-309.	1.1	5
342	Effect of graded buffer design on the defect structure in InGaAs/GaAs (111)B heterostructures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 80, 27-31.	1.7	5

#	Article	IF	Citations
343	Intensity noise in quantum-dot laser diodes. Applied Physics Letters, 2001, 78, 3577-3579.	1.5	5
344	Metastable rocksalt phase in epitaxial GaN on sapphire. Applied Physics Letters, 2003, 83, 2808-2810.	1.5	5
345	The polaronic nature of intraband relaxation in InAs/GaAs self-assembled quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 408-412.	1.3	5
346	Critical barrier thickness for the formation of InGaAs/GaAs quantum dots. Materials Science and Engineering C, 2005, 25, 798-803.	3.8	5
347	An approach to the formation mechanism of the composition fluctuation in GaInNAs quantum wells. Semiconductor Science and Technology, 2005, 20, 1096-1102.	1.0	5
348	Reduced temperature sensitivity of lasing wavelength in near-1.3â€…[micro sign]m InAs/GaAs quantum-dot laser with stepped composition strain-reducing layer. Electronics Letters, 2007, 43, 670.	0.5	5
349	Magnetic field tuning of hot electron resonant capture in a semiconductor device. Applied Physics Letters, 2007, 91, 142104.	1.5	5
350	Double transit region Gunn diodes. Semiconductor Science and Technology, 2007, 22, 245-248.	1.0	5
351	High-performance 1300-nm InAs/GaAs quantum-dot lasers. , 2008, , .		5
352	Voltage-controlled nuclear polarization switching in a singleInxGa1â^'xAsquantum dot. Physical Review B, 2009, 79, .	1.1	5
353	Thermal runaway and optical efficiency in InAs/GaAs quantum dot lasers. Applied Physics Letters, 2009, 95, 141106.	1.5	5
354	Dependence of N incorporation into (Ga)InAsN QDs on Ga content probed by rapid thermal annealing. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1441-1444.	0.8	5
355	Enhancement of activation energies of sharp photoluminescence lines for GaInNAs quantum wells due to quantum confinement. Journal Physics D: Applied Physics, 2013, 46, 402001.	1.3	5
356	Photoluminescence upconversion at<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>GaAs</mml:mi><mml:mo>/</mml:mo><mml:mi>InGa</mml:mi><mml:mathvariant="normal">P</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math>interfaces driven by a sequential two-photon absorption mechanism. Physical Review B, 2016, 93, .	1.1	5
357	Thermodynamic processes on a semiconductor surface during inâ€‰situ multiâ€beam laser interference patterning. IET Optoelectronics, 2019, 13, 7-11.	1.8	5
358	Mobility and saturation drift velocity enhancement in highly doped GaAs and InxGa1â€“xAs structures designed for use in power FET devices. Electronics Letters, 1996, 32, 494.	0.5	5
359	Quasiballistic electron transport in InP/InGaAs heterojunction bipolar transistors. Electronics Letters, 1992, 28, 145.	0.5	4
360	A comparison of 1.55 mu m distributed Bragg reflector stacks for use in multi quantum well micro resonator modulators. Semiconductor Science and Technology, 1995, 10, 1283-1286.	1.0	4

#	Article	IF	Citations
361	Investigation of g-factors Zeeman splittings, exchange interactions and field-dependent spin relaxation in IIIâ€“V quantum wells. Surface Science, 1996, 361-362, 435-438.	0.8	4
362	Incorporation of As2 in InAsxP1 â˜' x and its application to quantum well structures. Journal of Crystal Growth, 1997, 175-176, 1033-1038.	0.7	4
363	Structural and morphological characteristics of InGaAs/GaAs quantum well structures on tilted (111)B GaAs grown by MBE. Journal of Crystal Growth, 1998, 192, 363-371.	0.7	4
364	1.3 Âµm InAsP quantum well lasers grown by solid source MBE. IEE Proceedings: Optoelectronics, 1998, 145, 3-6.	0.8	4
365	Investigation of delta-doped quantum wells for power FET applications. Superlattices and Microstructures, 1998, 23, 187-190.	1.4	4
366	2.7 [micro sign]m LEDs for water vapour detection grown by MBE on InP. Electronics Letters, 1998, 34, 1606.	0.5	4
367	Optical monitoring of InP monolayer growth rates. Applied Physics Letters, 1998, 73, 345-347.	1.5	4
368	Strain-induced quantum confinement of electron gases: The observation of quantum dot levels. Applied Physics Letters, 1998, 73, 1898-1900.	1.5	4
369	Relaxation study of InxGa1â˜'xAs/GaAs quantum-well structures grown by MBE on (001) and (111)B GaAs for long wavelength applications. Journal of Crystal Growth, 1999, 206, 287-293.	0.7	4
370	Excitation and Relaxation Mechanisms in Single In(Ga)As Quantum Dots. Physica Status Solidi (B): Basic Research, 2001, 224, 373-378.	0.7	4
371	Recombination of Many-Particle States in InAs Self-Organized Quantum Dots. Physica Status Solidi (B): Basic Research, 2001, 224, 409-412.	0.7	4
372	Observation of in-plane polarized intersublevel absorption in strongly coupled InGaAs/GaAs self assembled quantum dots. Physica Status Solidi (B): Basic Research, 2003, 238, 341-344.	0.7	4
373	Tuning of electronic coupling between self-assembled quantum dots. Applied Physics Letters, 2005, 87, 033104.	1.5	4
374	High power and very low noise operation at 1.3 and 1.5 Î¼m with quantum dot and quantum dash Fabry-Perot lasers for microwave links. , 2006, 6399, 158.		4
375	High performance 2.2â€‰Î¼m optically-pumped vertical external-cavity surface-emitting laser. Journal of Modern Optics, 2007, 54, 1677-1683.	0.6	4
376	Intensity noise of ultrabroadband quantum dot light emitting diodes and lasers at 1.3 Î¼m. , 2007, , .		4
377	High Resolution HAADF-STEM Imaging Analysis of N related defects in GaNAs Quantum Wells. Microscopy and Microanalysis, 2008, 14, 318-319.	0.2	4
378	Tailoring the electrical conductivity of GaAs by nitrogen incorporation. Journal of Physics Condensed Matter, 2009, 21, 174209.	0.7	4

#	Article	IF	Citations
379	GaAs(001) (2Ã—4) to c(4Ã—4) transformation observed in situ by STM during As flux irradiation. Surface Science, 2009, 603, 2398-2402.	0.8	4
380	Quantitative investigation of the onset of islanding in strained layer epitaxy of InAs/GaAs by X-ray mapping in STEM. Journal of Physics: Conference Series, 2010, 209, 012035.	0.3	4
381	InAsP-based quantum wells as infrared pressure gauges for use in a diamond anvil cell. Journal of Applied Physics, 2012, 112, 074504.	1.1	4
382	Investigating the Capping of InAs Quantum Dots by InGaAs. Springer Proceedings in Physics, 2008, , 259-262.	0.1	4
383	Photoluminescence properties of a-(Si/SiN):H multilayers: A comparison with bulk alloys. Journal of Non-Crystalline Solids, 1987, 97-98, 883-886.	1.5	3
384	Quantum-confined Stark effect in InGaAs/InP multiple quantum wells grown by solid source molecular beam epitaxy. Journal of Crystal Growth, 1991, 111, 1080-1083.	0.7	3
385	Visible vertical cavity surface emitting lasers at Î» < 650 nm. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1995, 35, 12-16.	1.7	3
386	Photoconductivity studies of InAsP/InP heterostructures in applied magnetic and electric fields. Semiconductor Science and Technology, 1996, 11, 34-38.	1.0	3
387	Optical properties of InxGa1âˆ’xAs/GaAs MQW structures on (111)B GaAs grown by MBE: dependence on substrate miscut. Journal of Crystal Growth, 1999, 201-202, 1085-1088.	0.7	3
388	Influence of substrate misorientation on the structural characteristics of InGaAs/GaAs MQW on (111)B GaAs grown by MBE. Thin Solid Films, 1999, 343-344, 558-561.	0.8	3
389	Improved performance from GaAsâ€“AlGaAs quantum cascade lasers with enhanced upper laser level confinement. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 8-11.	1.3	3
390	InAsâ€“GaAs self-assembled quantum dot lasers: physical processes and device characteristics. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 489-493.	1.3	3
391	Crack initiation and termination in III-V epitaxial layers. Philosophical Magazine, 2003, 83, 3077-3092.	0.7	3
392	A ballistic electron emission microscopy study of ferromagnetic thin films embedded in Au/GaAs(100). Journal of Physics Condensed Matter, 2003, 15, 6485-6492.	0.7	3
393	Carrier distribution, spontaneous emission, and gain in self-assembled quantum dot lasers. , 2004, 5365, 86.		3
394	Structural defects characterisation of GaInNAs MQWs by TEM and PL. IEE Proceedings: Optoelectronics, 2004, 151, 385-388.	0.8	3
395	Temperature dependence of carrier dynamics in an inhomogeneous array of quantum dots. , 2004, 5452, 33.		3
396	Enhanced optical and structural properties of 1.3Î¼m GaInNAsâ•GaAs multiple quantum-well heterostructures with stepped strain-mediating layers. Applied Physics Letters, 2005, 86, 062107.	1.5	3

#	Article	IF	Citations
397	Time-resolved photoluminescence measurements of InAs self-assembled quantum dots (Invited Paper). , 2005, , .		3
398	Effect of GaAs polycrystal on the size and areal density of InAs quantum dots in selective area molecular beam epitaxy. Journal of Crystal Growth, 2006, 297, 38-43.	0.7	3
399	Spectroscopic evaluation of the structural and compositional properties of GaNxAs1âˆ'x superlattices grown by molecular beam epitaxy. Thin Solid Films, 2007, 515, 4430-4434.	0.8	3
400	Dynamics of carriers photogenerated in a dot-in-a-well nanostructure. Laser Physics, 2007, 17, 305-309.	0.6	3
401	Anomalous photocurrent in self-assembled InAsâ•GaAs quantum dots. Applied Physics Letters, 2008, 92, 182102.	1.5	3
402	Magneto-optical study of thermally annealed InAs-InGaAs-GaAs self-assembled quantum dots. Journal of Applied Physics, 2009, 105, 053512.	1.1	3
403	Voltage-controlled motional narrowing in a semiconductor quantum dot. New Journal of Physics, 2009, 11, 093032.	1.2	3
404	Electric field effects on the carrier migration in self-assembled InAs/GaAs quantum dots. Microelectronics Journal, 2009, 40, 838-840.	1.1	3
405	Control of Strain in GaSbAs/InAs/GaAs Quantum Dots. Journal of Physics: Conference Series, 2010, 245, 012065.	0.3	3
406	InAs/GaAs(001) molecular beam epitaxial growth in a scanning tunnelling microscope. Journal of Physics: Conference Series, 2010, 209, 012048.	0.3	3
407	Electrical characterisation of p-doped distributed Bragg reflectors in electrically pumped GaInNAs VCSOAs for 1.3Î¼m operation. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2012, 177, 739-743.	1.7	3
408	Gain characteristic of dilute nitride HELLISH-VCSOA for 1.3 Âµm wavelength operation. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 564-566.	0.8	3
409	Photonic Crystal Cavity-Based Intensity Modulation for Integrated Optical Frequency Comb Generation. Crystals, 2019, 9, 493.	1.0	3
410	Optical Frequency Comb Generation via Cascaded Intensity and Phase Photonic Crystal Modulators. IEEE Journal of Selected Topics in Quantum Electronics, 2021, 27, 1-9.	1.9	3
411	Application of anodic oxidation for postgrowth tailoring of InGaAsP/InP asymmetric Fabry-Perot modulator reflection spectra. Electronics Letters, 1995, 31, 1186.	0.5	3
412	Low avalanche noise behaviour in bulk Al/sub 0.8/Ga/sub 0.2/As. , 0, , .		2
413	Epitaxial Island Growth and the Stranski-Krastanow Transition. Materials Research Society Symposia Proceedings, 2001, 696, 1.	0.1	2
414	Optical Spectroscopic Study of Carrier Processes in Self-Assembled In(Ga)As-Ga(Al)As Quantum Dot Lasers. Physica Status Solidi (B): Basic Research, 2001, 224, 123-127.	0.7	2

#	Article	IF	Citations
415	Electrically pumped InGaAs quantum dot ring and cylindrical cavity lasers. Electronics Letters, 2001, 37, 1220.	0.5	2
416	Dynamics of stimulated emission in InAs quantum-dot laser structures measured in pump-probe experiments. Applied Physics Letters, 2002, 81, 4118-4120.	1.5	2
417	Relaxation study of AlGaAs cladding layers in InGaAs/GaAs (111)B lasers designed for 1.0â€“1.1Î¼m operation. Microelectronics Journal, 2002, 33, 553-557.	1.1	2
418	Investigations of 1.55-Î¼m GaInNAs/GaAs heterostructures by optical spectroscopy. IEE Proceedings: Optoelectronics, 2004, 151, 331-334.	0.8	2
419	Improvement in the optical quality of GaInNAs/GaInAs quantum well structures by interfacial strain reduction. IEE Proceedings: Optoelectronics, 2004, 151, 301-304.	0.8	2
420	High pressure as a tool to tune electronic coupling in self-assembled quantum dot nanostructures. Physica Status Solidi (B): Basic Research, 2004, 241, 3257-3262.	0.7	2
421	Polaron decay and inter-level transfer in InAs/GaAs self-assembled quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 2613-2616.	0.8	2
422	Systematic reduction of the permanent exciton dipole for charged excitons in individual self-assembled InGaAs quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 199-203.	1.3	2
423	Growth and characterization of multiple layer quantum dot lasers. , 2005, , .		2
424	Influence of In composition on the photoluminescence emission of In(Ga)As quantum dot bilayers. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 124-128.	1.3	2
425	Enhanced photoluminescence intensity of 1.3-Î¼m multi-layer InAs/InGaAs dots-in-well structure using the high growth temperature spacer layer step. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 129-132.	1.3	2
426	Integration of a resonant tunneling diode and an optical communications laser. , 2005, , .		2
427	Electric field induced blueshift of the e1-hh1 exciton transition in a GaAs1â^'xNxâ^•GaAs (x<1%) stepped quantum well. Applied Physics Letters, 2006, 89, 261110.	1.5	2
428	High Power, Very Low Noise, C.W. Operation of 1.32Î¼m Quantum-Dot Fabry-Perot Laser Diodes. , 2006, , .		2
429	The control of size and areal density of InAs self-assembled quantum dots in selective area molecular beam epitaxy on GaAs (001) surface. Microelectronics Journal, 2006, 37, 1505-1510.	1.1	2
430	Maximising the gain: optimising the carrier distribution in InGaAs quantum dot lasers. , 2007, , .		2
431	The use of Abellâ€“Tersoff potentials in atomistic simulations of InGaAsSb/GaAs. Optical and Quantum Electronics, 2008, 40, 1143-1148.	1.5	2
432	Low-Threshold 1.3-mum GaInNAs Quantum-Well Lasers Using Quaternary-Barrier Structures. IEEE Photonics Technology Letters, 2008, 20, 942-944.	1.3	2

#	Article	IF	Citations
433	High power, broad spectral width, 1300nm quantum-dot superluminescent diodes. , 2008, , .		2
434	Selective disordering of InAs/InGaAs dots-in-a-well structure patterned with sol-gel derived SiO2 strips imprinted by soft mold technique. Applied Physics Letters, 2008, 93, 071907.	1.5	2
435	Towards coherent optical control of a single hole spin: Rabi rotation of a trion conditional on the spin state of the hole. Solid State Communications, 2009, 149, 1458-1465.	0.9	2
436	Empirical bond order potential calculations of the elastic properties of epitaxial InGaSbAs layers. Microelectronics Journal, 2009, 40, 533-536.	1.1	2
437	InAs/GaAs quantum dots morphology: Nanometric scale HAADF simulations. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 165, 88-93.	1.7	2
438	Two-state passive mode-locking of quantum dot semiconductor lasers: Classical state scenario and novel reverse state dynamics. , 2010, , .		2
439	Recent progress in short wavelength quantum cascade lasers. , 2011, , .		2
440	Generation of optical frequency combs using a photonic crystal cavity. IET Optoelectronics, 2019, 13, 23-26.	1.8	2
441	Photonic integration of uniform GaAs nanowires in hexagonal and honeycomb lattice for broadband optical absorption. AIP Advances, 2020, 10, .	0.6	2
442	Comparing InGaAs and GaAsSb Metamorphic Buffer Layers on GaAs Substrates for InAs Quantum Dots Emitting at 1.55Î¼m. Springer Proceedings in Physics, 2008, , 263-268.	0.1	2
443	Transient photoluminescence in GaInAs/InP multiple quantum wells. Semiconductor Science and Technology, 1993, 8, 1758-1763.	1.0	1
444	Enhanced mobility piezoelectric AlInAs/InGaAs quantum well structures on (111)B InP substrates. Electronics Letters, 1995, 31, 2215-2216.	0.5	1
445	Strain-balanced quantum wells for power FET applications. , 0, , .		1
446	Optical spectroscopic determination of the electronic band structure of bulk AlGaInP and GaInP-AlGaInP heterojunction band offsets. , 1997, , .		1
447	Magneto-optics of zero-dimensional electron systems. Physica E: Low-Dimensional Systems and Nanostructures, 1997, 1, 191-197.	1.3	1
448	Inversion of electron sub-band population in a GaAs/AlGaAs triple barrier tunnelling structure. Solid-State Electronics, 1998, 42, 1533-1537.	0.8	1
449	Fermi-edge singularities in a one-dimensional electron system in magnetic field. Solid State Communications, 2001, 119, 55-58.	0.9	1
450	Temperature Dependent Optical Properties of InAs/AlGaAs Quantum Dots. Physica Status Solidi (B): Basic Research, 2001, 224, 107-110.	0.7	1

#	Article	IF	Citations
451	Fuchsâ€“Kliewer phonon excitations in GaNAs alloys. Journal of Applied Physics, 2004, 95, 8466-8468.	1.1	1
452	Influence of structure and defects on the performance of dot-in-well laser structures. , 2005, , .		1
453	Characterization of structure and defects in dot-in-well laser structures. Materials Science and Engineering C, 2005, 25, 793-797.	3.8	1
454	Capacitance-voltage measurements in InAs-GaAs self-assembled quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 3163-3166.	0.8	1
455	Determination Of InAsP/InP And InGaAs/InP Band Offsets Using Blue Shifting Type II Asymmetric Multiple Quantum Wells. AIP Conference Proceedings, 2005, , .	0.3	1
456	Quantum-dots in micro-pillar micro-cavities: experiment and theory. , 0, , .		1
457	Broad-band superluminescent light emitting diodes incorporating quantum dots in compositionally modulated quantum wells. , 2006, , .		1
458	Experiments Versus Modelling in Quantum Dot Pillar Microcavities. , 2006, , .		1
459	GROWTH AND CHARACTERIZATION OF MULTI-LAYER 1.3 Î¼m QUANTUM DOT LASERS. International Journal of Nanoscience, 2007, 06, 291-296.	0.4	1
460	The effects of monolayer thickness and sheet doping density on dark current and noise current in quantum dot infrared photodetectors. Proceedings of SPIE, 2007, , .	0.8	1
461	GaInNAs Lattice-Matched to GaAs for Photodiodes. Indium Phosphide and Related Materials Conference (IPRM), IEEE International Conference on, 2007, , .	0.0	1
462	Optical characterization of (In,Ga)(As,N) thin films grown by molecular beam epitaxy on non-(100) GaAs substrates. Journal of Crystal Growth, 2007, 301-302, 552-555.	0.7	1
463	A Quantum Dot Swept Laser Source Based upon a Multisection Laser Device. Japanese Journal of Applied Physics, 2008, 47, 2965-2967.	0.8	1
464	Short-wavelength quantum cascade lasers. , 2008, , .		1
465	As-rich reconstruction stability observed by high temperature scanning tunnelling microscopy. Journal of Crystal Growth, 2009, 311, 4478-4482.	0.7	1
466	Twoâ€colour photocurrent detection technique for coherent control of a single InGaAs/GaAs quantum dot. Physica Status Solidi (B): Basic Research, 2009, 246, 824-827.	0.7	1
467	Short Wavelength InP Based Quantum Cascade Lasers. , 2010, , .		1
468	Electroluminescence Studies of Modulation p-Doped Quantum Dot Laser Structures. IEEE Journal of Quantum Electronics, 2010, 46, 1847-1853.	1.0	1

#	Article	IF	Citations
469	Microcavity quantum-dot systems for non-equilibrium Bose-Einstein condensation. Journal of Physics: Conference Series, 2010, 245, 012059.	0.3	1
470	Reverse ground-state excited-state emission transition dynamics in two-section quantum dot semiconductor lasers: Simultaneous twostate mode-locking and state-switching via a resistor Self-Electro-optic Effect Device (SEED). , 2010, , .		1
471	All-optical switch using InAs quantum dots in a vertical cavity. , 2010, , .		1
472	In situ control and monitoring of photonic device intermixing during laser irradiation. Optics Express, 2011, 19, 9535.	1.7	1
473	Strongly coupled single quantum dot in a photonic crystal waveguide cavity. AIP Conference Proceedings, 2011, , .	0.3	1
474	Tunable spectral response by hydrogen irradiation of Ga(AsN) superlattice diodes. Applied Physics Letters, 2014, 104, 242110.	1.5	1
475	Control of quality factor in laterally coupled vertical cavities. IET Optoelectronics, 2020, 14, 100-103.	1.8	1
476	Temperature Dependent Optical Properties of InAs/AlGaAs Quantum Dots. Physica Status Solidi (B): Basic Research, 2001, 224, 107-110.	0.7	1
477	Directed self-assembly of InAs quantum dots using in situ interference lithography. , 2020, , .		1
478	Fine Structure of the Localized Emission from GaInNAs Layers Studied by Micro-Photoluminescence. Acta Physica Polonica A, 2009, 116, 930-932.	0.2	1
479	Electronic Properties of InAs/GaAs Self-Assembled Quantum Dot Structures and Devices Studied by Photocurrent Spectroscopy. Acta Physica Polonica A, 2000, 98, 279-293.	0.2	1
480	Mid-Infrared Optical Coherence Tomography: Application in Tissue Engineering. , 2006, , .		1
481	Room Temperature InGaAs-AlAsSb Quantum Cascade Lasers Operating in 3 â€“ 4 Âµm Range. , 2009, , .		1
482	Quantum Dot Switches: Towards Nanoscale Power-Efficient All-Optical Signal Processing. , 2012, , 197-221.		1
483	The band gap of â€˜â€˜perfectly disorderedâ€™â€™ Ga0.52In0.48P. AIP Conference Proceedings, 1994, , .	0.3	0
484	Magnetic field effects on InP/InGaAs quasiballistic heterojunction bipolar transistors. Semiconductor Science and Technology, 1994, 9, 1153-1155.	1.0	0
485	Exciton effects in strain-balanced GaInAs/AlInAs and GaInAs/GaInAs coupled quantum wells. Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics, 1995, 17, 1607-1612.	0.4	0
486	In/sub x/Ga/sub 1-x/As/InP multiquantum well structures grown on [111]B InP substrates. , 0, , .		0

#	Article	IF	Citations
487	Breakdown characteristics of (Al/sub X/Ga/sub 1-X/)/sub 0.52/In/sub 0.48/P p-i-n diodes. , 0, , .		0
488	Wannier-Stark ladder spectra in InxGa1â^'xAsî—¸GaAs strained layer piezo-electric superlattices. Solid-State Electronics, 1996, 40, 167-170.	0.8	0
489	Avalanche multiplication in sub-micron Al/sub x/Ga/sub 1-x/As/GaAs heterostructures. , 1997, , .		0
490	Band offsets in near-GaAs alloys. , 1997, , .		0
491	Investigation of band non-parabolicities in strain-balanced GaInAs/GaAlInAs coupled quantum wells. Superlattices and Microstructures, 1997, 22, 517-520.	1.4	0
492	Strain-induced quantum confinement of electron gases. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 2, 272-276.	1.3	0
493	Population inversion and intersubband electroluminescence in GaAs/AlGaAs triple barrier tunnelling structures. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 2, 473-477.	1.3	0
494	Magneto-optical spectroscopy of InAs/GaAs self-organised quantum dots. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 2, 689-693.	1.3	0
495	Optical investigation of strain-balanced superlattices. Superlattices and Microstructures, 1999, 25, 413-417.	1.4	0
496	Photocurrent Spectroscopy of InAs/GaAs Self-Assembled Quantum Dots: Observation of a Permanent Dipole Moment. Materials Research Society Symposia Proceedings, 1999, 571, 147.	0.1	0
497	Intrinsic performance of InGaAs-GaAs quantum dot lasers. , 0, , .		0
498	Temperature dependence of the wavelength of quantum dot lasers. , 0, , .		0
499	GaAs-AlGaAs and InGaAs-InAlAs quantum cascade lasers. , 2000, , .		0
500	Al0.8Ga0.2As: A very low excess noise multiplication medium for avalanche photodiodes. IEE Proceedings: Optoelectronics, 2001, 148, 243-246.	0.8	0
501	<title>Avalanche multiplication noise in bulk and thin Al<formula><inf><roman>(x)</roman></inf></formula>Ga<formula><inf><roman>(1-x)</roman></inf></formula>As (x=0-0.8) PIN and NIP diodes</title>. , 2001, , .		0
502	GaAs-based quantum cascade lasers with native oxide-defined current confinement. Electronics Letters, 2002, 38, 75.	0.5	0
503	Strategies for reducing the emission wavelength of GaAsâ€"AlAs quantum cascade lasers. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 835-839.	1.3	0
504	The role of climb and glide in misfit relief of InGaAs/GaAs(111)B heterostructures. Microelectronics Journal, 2002, 33, 559-563.	1.1	0

#	Article	IF	Citations
505	Mode structure of quantum dot semiconductor lasers. , 2004, , .		0
506	Low noise GaAs-based avalanche photodiodes for long wavelength applications. , 0, , .		0
507	Composition fluctuations in GaInNAs multi-quantum wells. IEE Proceedings: Optoelectronics, 2004, 151, 271-274.	0.8	0
508	Probing the N-induced states in dilute GaAsN alloys by magneto-tunnelling. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 892-896.	1.3	0
509	AlAs-like TO-phonon dephasing time in high Al content AlGaAs. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 2686-2689.	0.8	0
510	1.55-/spl mu/m GaInNAs/GaAs multiple quantum wells with GaInNAs quaternary barrier and space layer. , 2004, , .		0
511	Anomalous dispersion with excitation wavelength of longitudinal optical phononâ€“plasmon coupled modes in n-InGaAs. Journal of Physics Condensed Matter, 2004, 16, 971-978.	0.7	0
512	Dynamics of stimulated emission in InAs quantum dot laser structures measured in pump-probe experiments. , 2004, , .		0
513	Broad-band superluminescent light emitting diodes incorporating quantum dots in compositionally modulated quantum wells. , 2005, , .		0
514	Spin-memory and anomalous polarization properties of single InGaAs/GaAs quantum dots. , 0, , .		0
515	Spinodal decomposition in GaInNAs/GaAs multi-quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 1292-1297.	0.8	0
516	Dilute Nitride Ga(AsN) Alloys: an Unusual Band Structure Probed by Magneto-Tunneling. AIP Conference Proceedings, 2005, , .	0.3	0
517	Electronic Coupling between Self-Assembled Quantum Dots Tuned by High Pressure. AIP Conference Proceedings, 2005, , .	0.3	0
518	Reflection and emission of Brillouin zone edge states for active photonic crystal waveguides. Journal of Optics, 2005, 7, S270-S275.	1.5	0
519	Growth and Characterization of 1.3Î¼m Multi-Layer Quantum Dots Lasers Incorporating High Growth Temperature Spacer Layers. AIP Conference Proceedings, 2005, , .	0.3	0
520	InGaAs-AlAsSb-InP quantum cascade lasers: performance and prospects. , 0, , .		0
521	The Mechanism of the Stranski-Krastanov Transition. , 2005, , 71-88.		0
522	Engineering spin-polarization dynamics in InGaAs dot-in-a-well (DWELL) structures. , 0, , .		0

#	Article	IF	Citations
523	Recombination processes in inas quantum dot lasers containing high growth temperature spacer layers operating at 1.3 μm. , 0, , .		0
524	Ultra thin Ni films on singular and vicinal GaAs substrates. , 2006, , .		0
525	Maximising the Gain and Minimising the Non-Radiative Recombination in 1.3Î¼m Quantum Dot Lasers. , 2006, , .		0
526	Design, fabrication, and operating characteristics of broadband quantum dot superluminescent diodes. , 2006, , .		0
527	High-Power and Broad-Band Quantum Dot SLDs for Optical Coherence Tomography. , 2006, , .		0
528	High sensitivity terahertz detector using two-dimensional electron gas absorber and tunnel junction contacts as a thermometer. , 2006, , .		0
529	Optimisation of quantum dot infrared photodetectors (QDIPs) for imaging applications. , 2006, , .		0
530	Effect of the Growth Temperature in the Composition Fluctuation of GaInNAs/GaAs Quantum Wells. Microscopy and Microanalysis, 2006, 12, 754-755.	0.2	0
531	Size, areal density and emission energy control of InAs self assemble quantum dots grown on GaAs by selective area molecular beam epitaxy. , 2006, , .		0
532	Characterisation of modulation doped quantum dot lasers. , 2006, , .		0
533	Optical study of resonant states in GaN x As1â^'x. Semiconductors, 2006, 40, 1162-1164.	0.2	0
534	Dilute nitride-based 1.3Î¼m high performance lasers. , 2006, , .		0
535	Improved 1.3 μm In(Ga)As quantum dot lasers by engineering the GaAs spacer layers. , 2006, , .		0
536	Control of nuclear spin in InGaAs quantum dots. , 2006, , .		0
537	1.3 μm emitting, self assembled quantum dot lasers. , 2006, , .		0
538	The effect of p - doping in In(Ga)As quantum dot lasers. , 2006, , .		0
539	Excess Noise and Avalanche Multiplication in InAlAs. , 2006, , .		0
540	Dephasing of polarons in InAs/GaAs self-assembled quantum dots. , 2006, , .		0

#	Article	IF	Citations
541	Broadband quantum cascade lasers and superluminescent diodes. , 2006, , .		0
542	Localised recombination in quantum dot structures. , 2006, , .		0
543	A Ballistic Electron Emission Microscopy (BEEM) Study of Metallic Multilayers. , 2006, , .		0
544	High Q values and polarised emission from microcavity pillars with elliptical cross-section. , 2006, , .		0
545	Identifying the origin of Non-Radiative Recombination in In(Ga)As Quantum Dot Lasers. Conference Proceedings - Lasers and Electro-Optics Society Annual Meeting-LEOS, 2007, , .	0.0	0
546	Photon Coupling Mechanism in 1.3-μm Quantum-Dot Lasers. , 2007, , .		0
547	Coherent control of single quantum dot exciton embedded in a photodiode. Journal of Modern Optics, 2007, 54, 1717-1722.	0.6	0
548	CQED-Enhanced Single Photon Sources From InGaAs Quantum Dots. , 2007, , .		0
549	Systematic study of the effects of δ-p-doping on 1.3μm dot-in-well lasers. , 2007, , .		0
550	PROBING THE SCATTERING POTENTIAL OF N-IMPURITIES IN GaAs BY MAGNETO-TUNNELING. International Journal of Modern Physics B, 2007, 21, 1600-1604.	1.0	0
551	Dynamics of exciton recombination in InAs Quantum Dots embedded in InGaAs/GaAs Quantum Well. , 2007, , .		0
552	Very low-threshold-current-density 1.34-μm gainnas/gaas quantum well lasers with a quaternary-barrier structure. , 2007, , .		0
553	Short Wavelength InGaAs-AlAsSb-InP Quantum Cascade Lasers. Conference Proceedings - Lasers and Electro-Optics Society Annual Meeting-LEOS, 2007, , .	0.0	0
554	Modes of the L3 defect cavity in InAs quantum dot photonic crystals. , 2007, , .		0
555	Very low-threshold-current-density 1.34-Â¿m GaInNAs/GaAs quantum well lasers with a quaternary-barrier structure. , 2007, , .		0
556	Fast intraband capture and relaxation in InAs/GaAs self-assembled quantum dots. , 2007, , .		0
557	InGaAs-AlAsSb quantum cascade lasers: towards 3 μm emission. , 2007, , .		0
558	Photon coupling mechanism in 1.3-μm quantum-dot lasers. , 2007, , .		0

#	Article	IF	Citations
559	Mapping of the Initial Volume at the Onset of Plasticity in Nanoindentation. Materials Research Society Symposia Proceedings, 2007, 1049, 1.	0.1	0
560	Electronic Structure of Long Wavelength (>1.3Î¼m) GaAsSb-capped InAs Quantum Dots. AIP Conference Proceedings, 2007, , .	0.3	0
561	Effects of spacer growth temperature on the optical properties of quantum dot laser structures. , 2007, , .		0
562	Role of Device Structure on the Performance of Quantum Dot Lasers. Conference Proceedings - Lasers and Electro-Optics Society Annual Meeting-LEOS, 2007, , .	0.0	0
563	Quantum Dot Superluminescent Diodes - Bandwidth Engineering and Epitaxy for High Powers. Indium Phosphide and Related Materials Conference (IPRM), IEEE International Conference on, 2007, , .	0.0	0
564	High-Quality-Factor WG Modes in Semiconductor Microcavity Pillars with Circular and Elliptical Cross Section. , 2007, , .		0
565	Systematic Study of the Effects of Modulation P-Doping on 1.3μM InAs/GaAs Dot-in-Well Lasers. , 2007, , .		0
566	Dynamics of exciton recombination in InAs quantum dots embedded in InGaAs/GaAs quantum well. , 2007, , .		0
567	Kinetic considerations on the phase separation of GaInNAs quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 1477-1480.	0.8	0
568	Electric field effect in the spin dynamics of self-assembled InAs/GaAs quantum dots. Journal of Magnetism and Magnetic Materials, 2007, 316, e52-e55.	1.0	0
569	Tuning and Modulation in Two Section Quantum Dot Lasers. , 2008, , .		0
570	The use of Abel-Tersoff potentials in atomistic simulations of InGaAsSb/GaAs. , 2008, , .		0
571	Multi-Contact Quantum Dot Superluminescent Diodes for Optical Coherence Tomography. , 2008, , .		0
572	Dark current mechanisms in bulk GaInNAs photodiodes. , 2008, , .		0
573	Multi-contact quantum dot superluminescent diodes for optical coherence tomography. , 2008, , .		0
574	1.3Â¿m Quantum Dot Self-Aligned Stripe Laser. , 2008, , .		0
575	Two section quantum dot devices for tuning and modulation. , 2008, , .		0
576	Comprehensive RF-domain spectral- and time-domain analysis of passively mode-locked two-section quantum-dot lasers emitting at 1.3 Î¼m. Proceedings of SPIE, 2008, , .	0.8	0

#	Article	IF	Citations
577	Whispering gallery modes in quantum dot micropillar cavities. , 2008, , .		0
578	Optical coherence tomography with high power quantum-dot superluminescent diodes. , 2009, , .		0
579	Controlling the coherence properties of quantum dot superluminescent light emitting diodes via frequency selective optical feedback. , 2009, , .		0
580	Joint theoretical and experimental investigations of the CW lasing and turn-on dynamics of a quantum-dot semiconductor laser. , 2009, , .		0
581	High power performances of broad bandwidths superluminescent diodes (SLDs) based on chirped-quantum-dot structures operating at 1100 and 1200 nm for optical coherence tomography (OCT) applications. , 2009, , .		0
582	DIRECT IMPRINTING OF SiO₂ WAVEGUIDE STRUCTURES ON GaAs AND ITS APPLICATION IN InAs/GaAs QUANTUM DOT INTERMIXING. International Journal of Nanoscience, 2009, 08, 107-111.	0.4	0
583	Cavity-enhanced polarization control and observation of off-resonant coupling in quantum dot nanocavities. , 2009, , .		0
584	Quantum dots in a vertical cavity for all-optical switching devices. , 2009, , .		0
585	Broad-band high power quantum dot superluminescent diodes. , 2009, , .		0
586	Multi-contact quantum dot superluminescent diodes for optical coherence tomography. , 2009, , .		0
587	Carrier Escape Dynamics in Multilayered Self-Assembled InAsâˆ•GaAs Quantum Dots. , 2010, , .		0
588	Flat-topped emission centred at 1 250 nm from quantum dot superluminescent diodes. South African Journal of Science, 2010, 105, .	0.3	0
589	Self-assembled InAs quantum dots within a vertical cavity structure for all-optical switching devices. Proceedings of SPIE, 2010, , .	0.8	0
590	Extended ground-state and excited-state emission-state control in a mode-locked two-section quantum dot laser. , 2011, , .		0
591	Direct Evidence Of Long Lived Trapped Carriers In InGaAsâˆ•GaAs Quantum Dots Studied Using Terahertz-activated Luminescence Measurements. , 2011, , .		0
592	Adiabatic rapid passage on a single exciton. AIP Conference Proceedings, 2011, , .	0.3	0
593	Splitting and lasing of whispering gallery modes in quantum dot micropillars. , 2011, , .		0
594	3D g-Factor Mapping: Fine Structure Effects in Single Quantum Dots. , 2011, , .		0

#	Article	IF	Citations
595	Impact of the Ga/In ratio on the N incorporation into (In,Ga)(As,N) quantum dots. Journal of Applied Physics, 2012, 111, 083530.	1.1	0
596	Polarization-resolved resonant fluorescence of a single semiconductor quantum dot. Applied Physics Letters, 2012, 101, 251118.	1.5	0
597	Intra-cavity absorber photocurrent characteristics of a quantum dot laser emitting on two emission-states: experiment and simulation. , 2012, , .		0
598	Study of controlled quantum dot formation on focused ion beam patterned GaAs substrates. , 2012, , .		0
599	Photoluminescence in Tilted Magnetic Field of Triply Negatively Charged Excitons Hybridized with a Continuum. Acta Physica Polonica A, 2013, 124, 798-800.	0.2	0
600	Investigations on photocurrent bi-stability of a two-color mode-locked quantum dot laser. , 2014, , .		0
601	Modulating Photonic Crystal Structures to Generate Optical Frequency Combs. , 2018, , .		0
602	Quality Factor Control in Laterally-Coupled Vertical Cavities. , 2018, , .		0
603	Quantum Dots: Site-Controlled Single-Photon Emitters Fabricated by Near-Field Illumination (Adv.) Tj ETQq1 1 0.784314 rgBT /Overlo	11.1	0
604	The Stark Effect and Electron-Hole Wavefunctions in InAs-GaAs Self-Assembled Quantum Dots. , 2000, , 337-346.		0
605	Shape analysis of single and stacked InAs quantum dots at the atomic level by cross-sectional STM. Springer Proceedings in Physics, 2001, , 359-360.	0.1	0
606	Transverse mode structure of broad area quantum dot edge emitting lasers emitting at 1060 nm. , 2003, , .		0
607	Fast Optical Preparation, Control, and Detection of a Single Hole Spin in a Quantum Dot. , 2008, , .		0
608	Controlled Rotation (C-ROT) Gate in a Single Self- Assembled Quantum Dot. , 2008, , .		0
609	Picosecond Coherent Control of Dressed States in a Single Quantum Dot. , 2009, , .		0
610	Robust Optical Inversion of the Excitonic Population of InGaAs Quantum Dots via Adiabatic Rapid Passage. , 2011, , .		0
611	Catastrophic Optical Damage in Quantum Dot Lasers. , 2012, , 93-108.		0
612	Delta-doping-enhanced InGaAs/InAlAs heterobarrier diodes. Electronics Letters, 1995, 31, 493-494.	0.5	0

#	Article	IF	Citations
613	Optimisation of the optical emission of bilayers of quantum dots. , 2018, , 103-106.		0
614	Strain relaxation behaviour in InxGa1-xAs quantum wells on misorientated GaAs (111)B substrates. , 2018, , 137-140.		0
615	Characterization of InGaAs (N)/GaAsN multi-quantum wells using transmission electron microscopy. , 2018, , 143-146.		0
616	Barrier thickness influence on plastic relaxation in (111)B misoriented InGaAs/GaAs double quantum wells. , 2018, , 133-136.		0
617	Vertical correlation-anticorrelation transition in InAs/GaAs quantum dot structures grown by molecular beam epitaxy. , 0, , 251-254.		0
618	Effect of annealing on anticorrelated InGaAs/GaAs quantum dots. , 0, , 255-258.		0
619	Structural analysis of the effects of a combined InAlAs-InGaAs capping layer in 1.3-Î¼m InAs quantum dots. , 0, , 263-266.		0
620	Microstructural studies of InAs/GaAs self-assembled quantum dots grown by selective area molecular beam epitaxy. , 0, , 267-270.		0
621	Activation energy for surface diffusion in GaInNAs quantum wells. , 0, , 279-282.		0
622	Influence of the Growth Temperature on the Composition Fluctuations of GaInNAs/GaAs Quantum Wells. , 2008, , 199-221.		0